

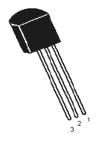
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General Purpose Transistor







Pin Configuration:

- 1. Emitter
- 2. Base
- 3. Collector

Description:

General purpose NPN silicon planar epitaxial transistors, best suited for use in driver stages of audio amplifiers, low noise input stages of tape recorders. Hi-Fi amplifiers, signal processing circuits of television receivers.

Absolute Maximum Ratings

Parameter	Symbol	Value	Units	
Collector-Emitter Voltage	V _{CEO}	45		
Collector-Emitter Voltage	V _{CES}	V		
Emitter-Base Voltage	$V_{\scriptscriptstyle{EBO}}$			
Collector Current Continuous	I _c	100	mA	
Power Dissipation at T _a = 25°C Derate Above 25°C		350 2.8	mW mW/°C	
Total Device Dissipation at T _c = 25°C Derate Above 25°C	P _D	1 8	W mW/°C	
Operating and Storage Junction Temperature Range	T_{j},T_{stg}	-55 to + 150 °C		

Thermal Resistance

Junction to Ambient	R _{th (j-a)}	375	°C/W	
Junction to Case	R _{th (j-c)}	125	C/VV	

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Electrical Characteristics ($T_a = 25$ °C unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Тур.	Max.	Units
Collector Emitter Voltage	V _{CEO}	$I_{\rm C} = 2\text{mA}, I_{\rm B} = 0$	45	1	-	V
Emitter Base Voltage	V _{EBO}	$I_{E} = 100 \mu A, I_{C} = 0$	6	1	-	V
Collector Cut off Current	I _{CES}	$V_{CE} = 50V, V_{BE} = 0$ $V_{CE} = 50V, V_{BE} = 0,$ $T_{a} = 125^{\circ}C$	-	ı	15 4	nΑ μΑ
DC Current Gain	h _{FE}	$I_{\rm C} = 2 {\rm mA}, V_{\rm CE} = 50 {\rm V}$	200	290	460	-
Collector Emitter Saturation Voltage	V _{CE (sat)}	$I_{\rm C} = 10$ mA, $I_{\rm B} = 0.5$ mA $I_{\rm C} = 100$ mA, $I_{\rm B} = 5$ mA*	-	0.07 0.2	0.2 0.6	
Base Emitter Saturation Voltage	V _{BE (sat)}	$I_{C} = 10 \text{mA}, I_{B} = 0.5 \text{mA}$ $I_{C} = 100 \text{mA}, I_{B} = 0.5 \text{mA}^{*}$	1	0.6	0.83 1.05	V
Base Emitter On Voltage	V _{BE (on)}	$I_{C} = 100 \mu A, V_{CE} = 5V$ $I_{C} = 2 m A, V_{CE} = 5 V$ $I_{C} = 100 m A, V_{CE} = 5 V^{*}$	0.55	0.5 0.62 0.83	0.7	

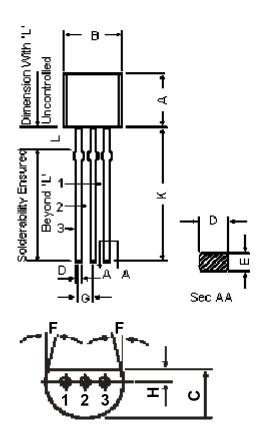
Dynamic Characteristics

Transition Frequency	f _T	$I_{c} = 0.5 \text{mA}, V_{cE} = 3V$ f = 100 MHz $I_{c} = 10 \text{mA}, V_{cE} = 5V$ f = 100 MHz	- 150	100 200	-	MHz
Collector Output Capacitance	C _{ob}	$V_{CB} = 10V, I_{E} = 0 f = 1MHz$	-	-	4.5	5E
Emitter Input Capacitance	C _{ib}	$V_{EB} = 0.5V, I_{E} = 0$ f = 1MHz	-	8	4.5	pF
Noise Figure	NF	V_{CE} = 5V, I_{C} = 2mA Rs = 2kW, f = 1kHz F = 200Hz	-	2	10	dB

^{*}Pulse Condition: Pulse Width 300µs, Duty Cycle 2%.

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Dimensions	Min.	Max.	
А	4.32	5.33	
В	4.45	5.2	
С	3.18	4.19	
D	0.41	0.55	
E	0.35	0.5	
F	5°		
G	1.14	1.4	
Н	1.14	1.53	
K	12.7	-	
L	1.982	2.082	

Dimensions: Millimetres

Pin Configuration:

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- 2. Base
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Part Number Table

Description	Part Number		
Transistor, NPN, TO-92	BC237B		

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